

Alessandro Grillo

List of Publications by Year in descending order

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33
papers

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citations

471509

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501196

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34
all docs

34
docs citations

34
times ranked

1118
citing authors

#	ARTICLE	IF	CITATIONS
1	Asymmetric Schottky Contacts in Bilayer MoS ₂ Field Effect Transistors. Advanced Functional Materials, 2018, 28, 1800657.	14.9	162
2	Pressure-Tunable Ambipolar Conduction and Hysteresis in Thin Palladium Diselenide Field Effect Transistors. Advanced Functional Materials, 2019, 29, 1902483.	14.9	98
3	Gas dependent hysteresis in MoS ₂ field effect transistors. 2D Materials, 2019, 6, 045049.	4.4	79
4	Field Emission in Ultrathin PdSe ₂ Back-Gated Transistors. Advanced Electronic Materials, 2020, 6, 2000094.	5.1	66
5	Contact resistance and mobility in back-gate graphene transistors. Nano Express, 2020, 1, 010001.	2.4	55
6	Coexistence of Negative and Positive Photoconductivity in Few-Layer PtSe ₂ Field-Effect Transistors. Advanced Functional Materials, 2021, 31, 2105722.	14.9	53
7	A Current-Voltage Model for Double Schottky Barrier Devices. Advanced Electronic Materials, 2021, 7, 2000979.	5.1	49
8	Electron Irradiation of Metal Contacts in Monolayer MoS ₂ Field-Effect Transistors. ACS Applied Materials & Interfaces, 2020, 12, 40532-40540.	8.0	44
9	WS ₂ Nanotubes: Electrical Conduction and Field Emission Under Electron Irradiation and Mechanical Stress. Small, 2020, 16, e2002880.	10.0	42
10	Graphene-Silicon Device for Visible and Infrared Photodetection. ACS Applied Materials & Interfaces, 2021, 13, 47895-47903.	8.0	41
11	Field Emission Characterization of MoS ₂ Nanoflowers. Nanomaterials, 2019, 9, 717.	4.1	40
12	Observation of 2D Conduction in Ultrathin Germanium Arsenide Field-Effect Transistors. ACS Applied Materials & Interfaces, 2020, 12, 12998-13004.	8.0	40
13	Gate-Controlled Field Emission Current from MoS ₂ Nanosheets. Advanced Electronic Materials, 2021, 7, 2000838.	5.1	37
14	High field-emission current density from $\text{In}^2\text{-Ga}_2\text{O}_3$ nanopillars. Applied Physics Letters, 2019, 114, .	3.3	33
15	Bias Tunable Photocurrent in Metal-Insulator-Semiconductor Heterostructures with Photoresponse Enhanced by Carbon Nanotubes. Nanomaterials, 2019, 9, 1598.	4.1	29
16	Graphene Schottky Junction on Pillar Patterned Silicon Substrate. Nanomaterials, 2019, 9, 659.	4.1	22
17	Field Emission Characteristics of InSb Patterned Nanowires. Advanced Electronic Materials, 2020, 6, 2000402.	5.1	18
18	Field emission from two-dimensional GeAs. Journal Physics D: Applied Physics, 2021, 54, 105302.	2.8	18

#	ARTICLE	IF	CITATIONS
19	Memory effects in black phosphorus field effect transistors. 2D Materials, 2022, 9, 015028.	4.4	17
20	Impact of Impurities on the Electrical Conduction of Anisotropic Two-Dimensional Materials. Physical Review Applied, 2020, 13, .	3.8	16
21	Environmental effects on transport properties of PdSe2 field effect transistors. Materials Today: Proceedings, 2020, 20, 50-53.	1.8	15
22	Effect of silicon doping on graphene/silicon Schottky photodiodes. Materials Today: Proceedings, 2020, 20, 82-86.	1.8	8
23	Persistent Photoconductivity, Hysteresis and Field Emission in MoS2 Back-Gate Field-Effect Transistors. , 2018, , .		5
24	Air Pressure, Gas Exposure and Electron Beam Irradiation of 2D Transition Metal Dichalcogenides. Applied Sciences (Switzerland), 2020, 10, 5840.	2.5	5
25	Field emission from mono and two-dimensional nanostructures. Materials Today: Proceedings, 2020, 20, 64-68.	1.8	4
26	Electrical transport in two-dimensional PdSe2 and Mos2 nanosheets. , 2020, , .		3
27	Electrical Conduction and Photoconduction in PtSe2 Ultrathin Films. Materials Proceedings, 2020, 4, .	0.2	2
28	2D transition metal dichalcogenides nanosheets as gate modulated cold electron emitters. , 2021, , .		1
29	Temperature Dependence of Germanium Arsenide Field-Effect Transistors Electrical Properties. Materials Proceedings, 2021, 4, 26.	0.2	1
30	Sensors Based on Multiwalled Carbon Nanotubes. Materials Proceedings, 2021, 4, 59.	0.2	1
31	Modification of contacts and channel properties in two-dimensional field-effect transistors by 10 keV electron beam irradiation. , 2021, , .		0
32	Molybdenum Disulfide Field Effect Transistors under Electron Beam Irradiation and External Electric Fields. Materials Proceedings, 2021, 4, 25.	0.2	0
33	Direct Contacting of 2D Nanosheets by Metallic Nanoprobes. Materials Proceedings, 2020, 4, .	0.2	0